

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,806,492 B2
DATED : October 19, 2004
INVENTOR(S) : Donghang Yan et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

The title page should be deleted and substitute therefor the attached title page as shown on the attached page.

Signed and Sealed this

Thirty-first Day of May, 2005

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looping initial "J" and a distinct "D" at the end.

JON W. DUDAS
Director of the United States Patent and Trademark Office

(12) **United States Patent**
Yan et al.

(10) Patent No.: **US 6,806,492 B2**
(45) Date of Patent: **Oct. 19, 2004**

(54) **HETEROJUNCTION ORGANIC
SEMICONDUCTOR FIELD EFFECT
TRANSISTOR (FET) WITH A GATE
INSULATION LAYER AND
MANUFACTURING PROCESS THEREOF**

(58) Field of Search 257/40, 192, 77,
257/347, 613, 289, 66; 438/99, 151, 158,
161

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(57) ABSTRACT

A organic semiconductor field effect transistor that can work in the depletion mode or super-inverse mode, comprising: a substrate (1), a gate electrode (2) formed on the substrate (1), a gate insulation layer (3) formed on the substrate (1) and the gate electrode (2), a first semiconductor layer (4) formed on the gate insulation layer (3), a source electrode and a drain electrode (5) formed on the first semiconductor layer (4), and a second semiconductor layer (6) formed on the first semiconductor layer (4) and the source/drain electrodes (5).

9 Claims, 5 Drawing Sheets

